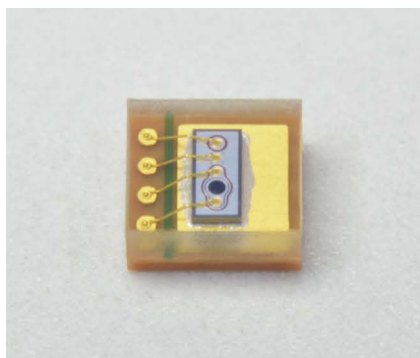


Si APD

S15413-02



High-speed, compact Si APD that does not require temperature adjustment

The S15413-02 is a gain-stabilized APD (GS APD) with a built-in temperature compensation function inside the sensor. This realizes constant gain without the need for temperature adjustment. It is suitable for laser monitors of optical rangefinders used in a wide range of applications, from consumer to industrial.

Features

- Built-in temperature compensation function
- Compact package: $2.0 \times 1.8 \times 0.85^t$ mm
- Peak sensitivity wavelength: 760 nm (M=50)
- High-speed response: Cutoff frequency=1.5 GHz typ. ($\lambda=660$ nm, M=50)

Applications

- Optical rangefinders

Structure

Parameter	Specification	Unit
Photosensitive area*1	$\phi 0.2$	mm
Package	Glass epoxy	-
Seal material	Silicone resin	-

*1: Area in which a typical gain can be obtained

Absolute maximum ratings

Parameter	Symbol	Specification	Unit
Anode reverse current (DC)	$I_{r \text{ anode max}}$	0.1	mA
Forward current	$I_F \text{ max}$	10	mA
Operating temperature*2	T_{opr}	-30 to +105	°C
Storage temperature*2	T_{stg}	-40 to +105	°C
Soldering temperature	T_{sol}	260 (3 times)*3	°C

*2: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

*3: Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

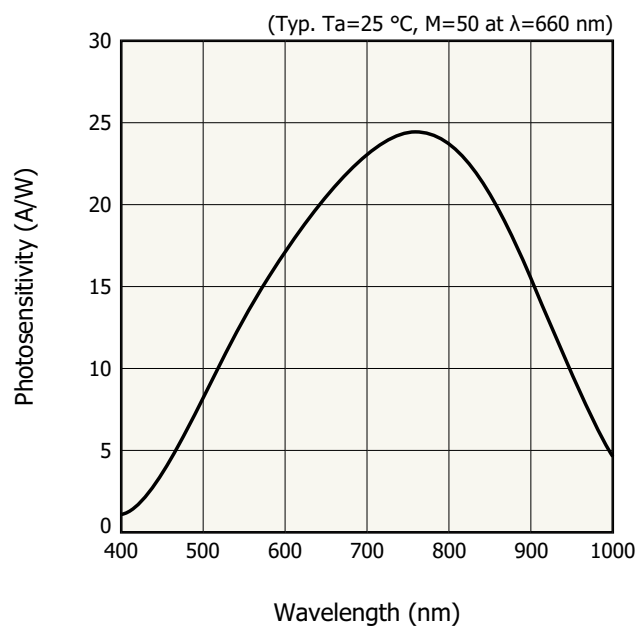
Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ			400 to 1000		nm
Peak sensitivity wavelength	λ_p		-	760	-	nm
Photosensitivity	S	$\lambda=660$ nm, M=1	-	0.42	-	A/W
Quantum efficiency	QE	$\lambda=660$ nm, M=1	-	85	-	%
Operating reverse voltage	Vop	Gain-stabilized mode operation*4	$110 + 0.42 \times (T_{a\text{ opr}} - 25)^{*5}$	-	-	V
Temperature coefficient of operating reverse voltage	$\Delta T V_{op}$		-	0.42	-	V/°C
Dark current	I _D	Gain-stabilized mode operation*4	-	10	100	pA
Dark current temperature coefficient	$\Delta T I_D$	M=50	-	1.1	-	times/°C
Cutoff frequency	f _c	M=50, R _L =50 Ω $\lambda=660$ nm, -3 dB	-	1.5	-	GHz
Terminal capacitance	C _t	M=50, f=1 MHz	-	0.6	-	pF
Excess noise figure	x	M=50, $\lambda=660$ nm	-	0.3	-	-
Gain	M	Gain-stabilized mode operation*4, $\lambda=660$ nm	40	50	60	-
Gain control range	-	$\lambda=660$ nm	-	30 to 100	-	-

*4: Apply bias voltage to anode. I_r anode limit=10 μ A, guard pin=GND

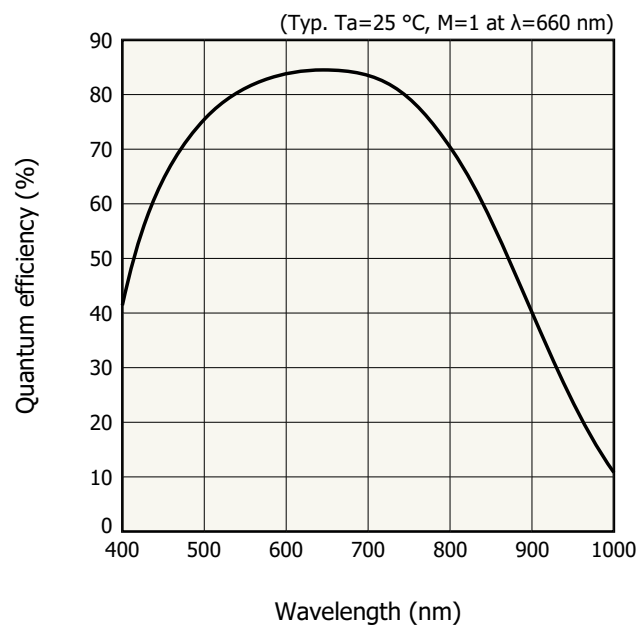
*5: T_{a opr}=assumed maximum operating temperature

Spectral response



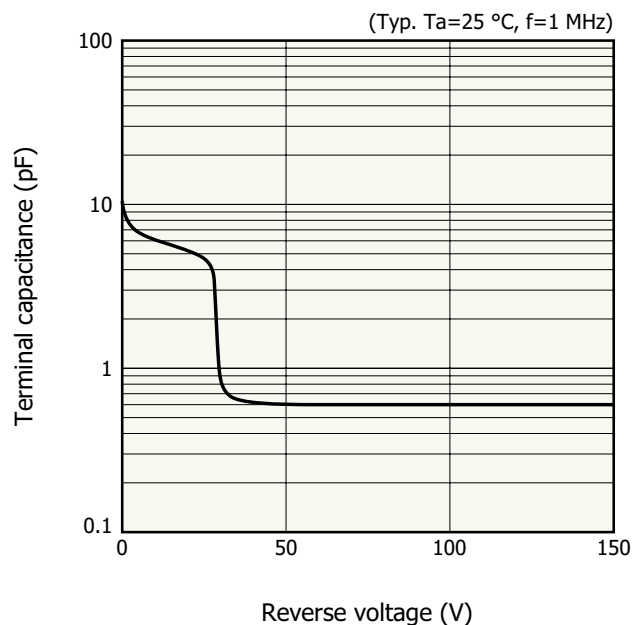
KAPDB0653EA

Quantum efficiency vs. wavelength



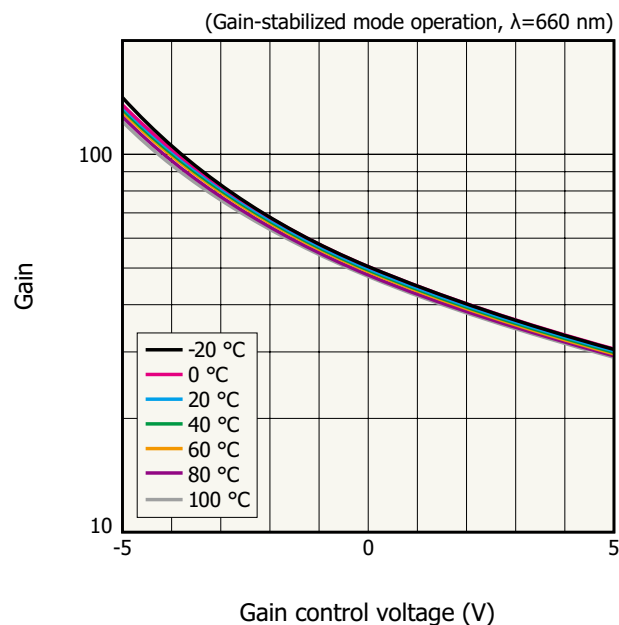
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Terminal capacitance vs. reverse voltage



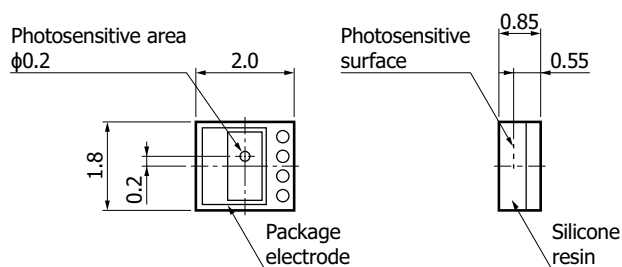
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Gain vs. gain control voltage (typical example)

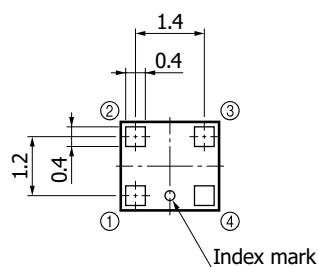
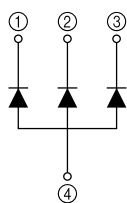


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Dimensional outlines (unit: mm)



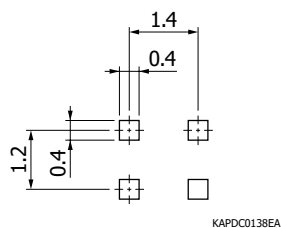
Tolerance unless otherwise noted: ± 0.2
 Chip position accuracy with respect to package electrode pattern center: $X, Y \leq \pm 0.2$



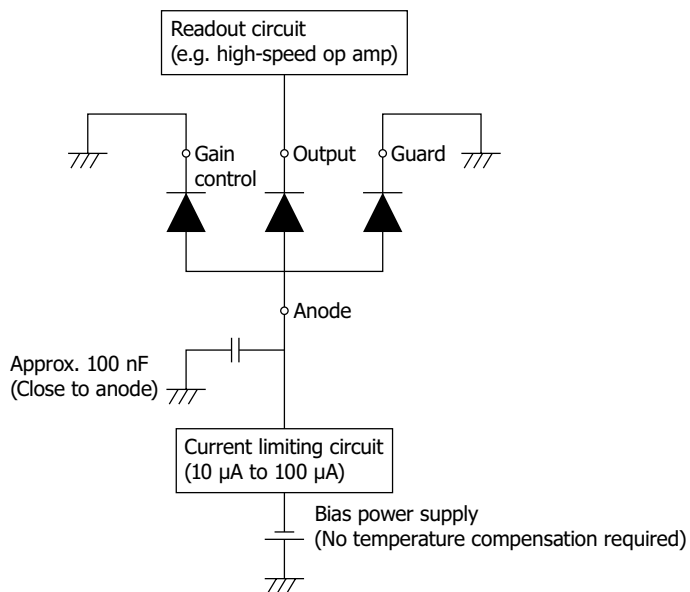
①	Gain control	Gain control voltage input (connect to GND)
②	Output	APD output
③	Guard	Leakage current output (connect to GND)
④	Anode	Bias voltage input

KAPDA0229EA

Recommended land pattern



Connection example



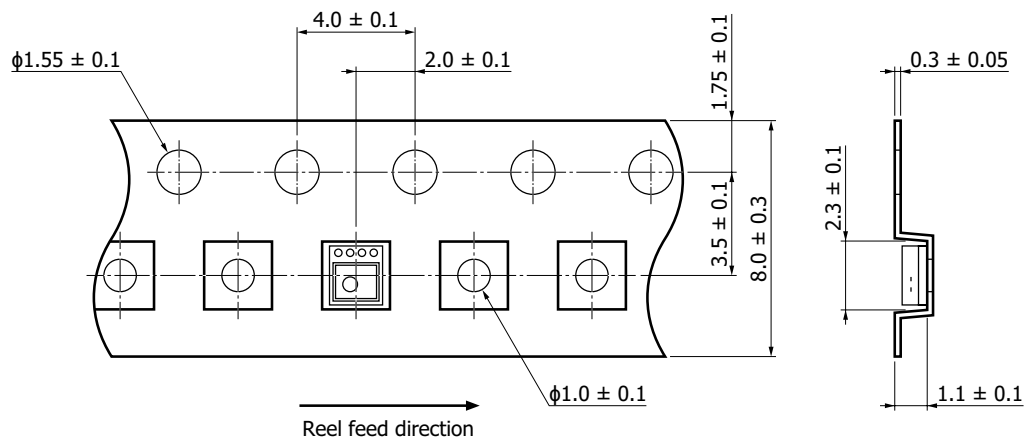
- KAPDC0137FR

Standard packing specifications

- Reel (conforms to JEITA ET-7200)

Appearance	Hub diameter	Tape width	Material	Electrostatic characteristics
φ180 mm	φ60 mm	8 mm	PS	Conductive

- Embossed tape (unit: mm, material: PS, conductive)



KAPDC0139EA

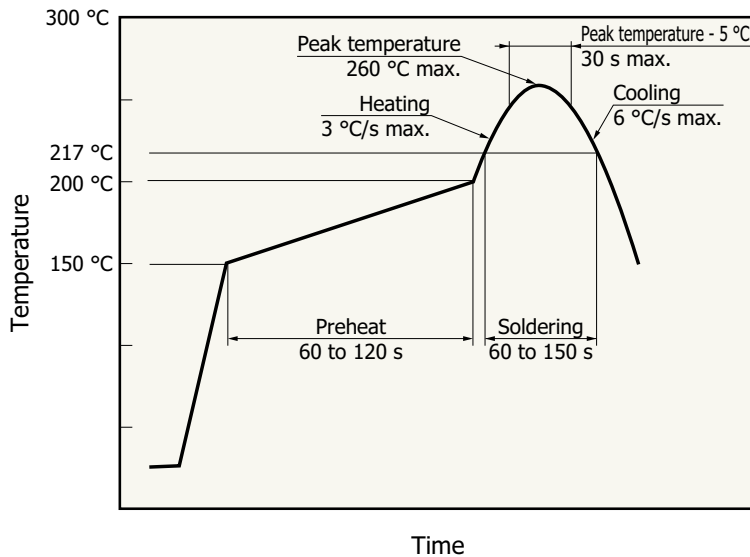
- Packing quantity

1000 pcs/reel

- Packing state

Reel and desiccant in moisture-proof packaging (vacuum-sealed)

Recommended reflow soldering conditions



- After unpacking, store in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform reflow soldering within 4 weeks.
- The effect that the product receives during reflow soldering varies depending on the circuit board and reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

Baking

If 12 months have passed without unpacking or the above storage period has passed after unpacking, perform baking before reflow soldering to dehumidify. For the baking, refer to "Precautions / Surface mount type products" in the related information.

Recommended baking conditions

- Temperature: 150 °C, 3 hours, up to twice

Note: When you set baking conditions, check that problems do not occur in the product by testing out the conditions in advance.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

Precautions

- Disclaimer
- Precautions / Surface mount type products

Catalogs

- Technical note / Si APD

The content of this document is current as of March 2025.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

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